

FX20ASJ-03F

High-Speed Switching Use Pch Power MOS FET

REJ03G0248-0100 Rev.1.00 Aug.20.2004

Features

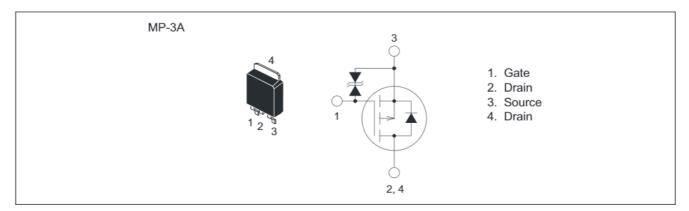
· Drive voltage: 4 V

• $V_{DSS}:-30~V$

• $r_{DS(ON) (max)}$: 0.12 Ω

I_D: −20 A

Outline



Applications

Motor control, lamp control, solenoid control, DC-DC converters, etc.

Maximum Ratings

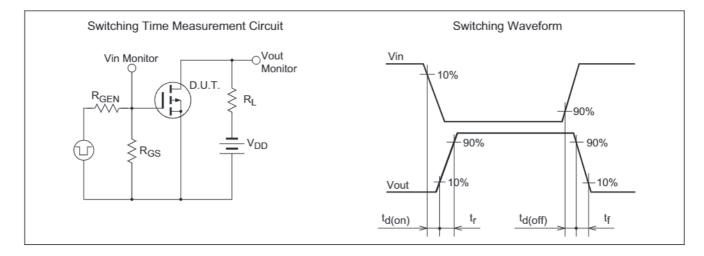
 $(Tc = 25^{\circ}C)$

Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V _{DSS}	-30	V	V _{GS} = 0 V
Gate-source voltage	V _{GSS}	±20	V	V _{DS} = 0 V
Drain current	I _D	-20	А	
Drain current (Pulsed)	I _{DM}	- 40	А	
Avalanche current (Pulsed)	I _{DA}	-5	А	L = 10 ∞H
Source current	Is	-20	А	
Source current (Pulsed)	I _{SM}	- 40	Α	
Maximum power dissipation	PD	25	W	
Channel temperature	Tch	- 55 to +150	°C	
Storage temperature	Tstg	- 55 to +150	°C	
Mass	_	0.32	g	Typical value

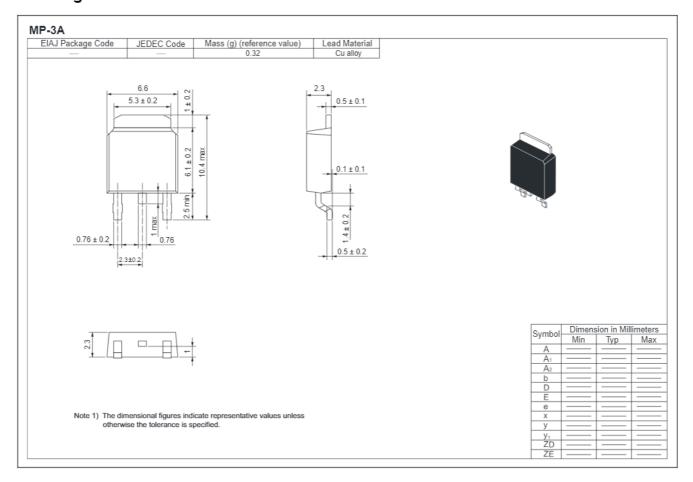
Electrical Characteristics

 $(Tch = 25^{\circ}C)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions	
Drain-source breakdown voltage	V _{(BR)DSS}	-30	_	_	V	I _D = 1 mA, V _{GS} = 0 V	
Gate-source breakdown voltage	V _{(BR)GSS}	±20	_	_	V	$I_G = \pm 100 \propto A, V_{DS} = 0 \text{ V}$	
Drain-source leakage current	I _{DSS}	_	_	100	«A	V _{DS} = -30 V, V _{GS} = 0 V	
Gate-source leakage current	I _{GSS}	_	_	±10	∞A	V _{GS} = ±20 V, V _{DS} = 0 V	
Gate-source threshold voltage	V _{GS(th)}	-1.5	-2.0	-2.5	V	I _D = -1 mA, V _{DS} = -10 V	
Drain-source on-state resistance	r _{DS(ON)}	_	0.085	0.12	Ω	I _D = -10 A, V _{GS} = -10 V	
Drain-source on-state resistance	r _{DS(ON)}	_	0.145	0.20	Ω	I _D = -2 A, V _{GS} = -4 V	
Drain-source on-state voltage	V _{DS(ON)}	_	-0.85	-1.2	V	I _D = -10 A, V _{GS} = -10 V	
Forward transfer admittance	y _{fs}	_	8	_	S	I _D = -10 A, V _{DS} = -5 V	
Input capacitance	Ciss	_	500	_	pF	V _{DS} = -10 V, V _{GS} = 0 V,	
Output capacitance	Coss	_	100	_	pF	f = 1MHz	
Reverse transfer capacitance	Crss	_	80	_	pF		
Turn-on delay time	t _{d(on)}	_	6	_	ns	V _{DD} = -15 V, I _D = -10 A,	
Rise time	t _r	_	8	_	ns	V _{GS} = -10 V,	
Turn-off delay time	t _{d(off)}	_	40	_	ns	$R_{GEN} = R_{GS} = 50 \Omega$	
Fall time	t _f	_	15	_	ns		
Source-drain voltage	V _{SD}	_	-1.0	-1.5	V	I _S = -10 A, V _{GS} = 0 V	
Thermal resistance	Rth(ch-c)	_	_	5.0	°C/W	Channel to case	
Reverse recovery time	t _{rr}	_	30	_	ns	I _S = -10 A, dis/dt = -50 A/x	



Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FX20ASJ-03F-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	FX20ASJ-03F

Note: Please confirm the specification about the shipping in detail.

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